MBR16100CTG

Switch-mode Power Rectifier

ON Semiconductor®

www.onsemi.com

SCHOTTKY BARRIER RECTIFIER 16 AMPERES, 100 VOLTS

Features and Benefits

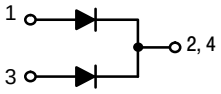
- Low Forward Voltage
- Low Power Loss/High Efficiency
- High Surge Capacity
- 175°C Operating Junction Temperature
- Low Stored Charge Majority Carrier Conduction
- 16 A Total (8.0 A Per Diode Leg)
- This Device is Pb−Free and is RoHS Compliant*

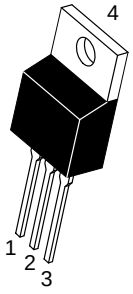
Applications

- Power Supply − Output Rectification
- Power Management
- Instrumentation

Mechanical Characteristics

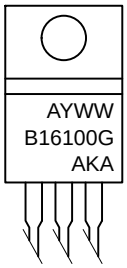
- Case: Epoxy, Molded
- Epoxy Meets UL 94 V−0 @ 0.125 in
- Weight: 1.9 Grams (Approximately)
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead Temperature for Soldering Purposes: 260°C Max. for 10 Seconds
- ESD Rating: Human Body Model = 3B
  Machine Model = C





TO−220
CASE 221A
STYLE 6

MARKING DIAGRAM



A	= Assembly Location
Y	= Year
WW	= Work Week
B16100	= Device Code
G	= Pb−Free Package
AKA	= Diode Polarity

ORDERING INFORMATION

Device	Package	Shipping
MBR16100CTG	TO−220 (Pb−Free)	50 Units/Rail

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

© Semiconductor Components Industries, LLC, 2015

MAXIMUM RATINGS (Per Diode Leg)

Rating	Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	100	V
Average Rectified Forward Current (T_C = 166°C) Per Diode Per Device	$I_{F(AV)}$	 8.0 16	A
Peak Repetitive Forward Current (Square Wave, 20 kHz) T_C = 165°C	I_{FRM}	16	A
Non-repetitive Peak Surge Current (Surge applied at rated load conditions half-wave, single phase, 60 Hz)	I_{FSM}	150	A
Peak Repetitive Reverse Surge Current (2.0 μs, 1.0 kHz)	I_{RRM}	0.5	A
Operating Junction Temperature (Note 1)	T_J	−65 to +175	°C
Storage Temperature	T_{stg}	−65 to +175	°C
Voltage Rate of Change (Rated V_R)	dv/dt	10,000	V/μs

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. The heat generated must be less than the thermal conductivity from Junction−to−Ambient: $dP_D/dT_J < 1/R_{\theta JA}$.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Value	Unit
Maximum Thermal Resistance, Junction−to−Case (Min. Pad) Junction−to−Ambient (Min. Pad)	$R_{\theta JC}$ $R_{\theta JA}$	2.0 60	°C/W

ELECTRICAL CHARACTERISTICS (Per Diode Leg)

Characteristic	Symbol	Min	Typical	Max	Unit
Maximum Instantaneous Forward Voltage (Note 2) (i_F = 8.0 A, T_J = 125°C) (i_F = 8.0 A, T_J = 25°C) (i_F = 16 A, T_J = 125°C) (i_F = 16 A, T_J = 25°C)	v_F	 − − − −	 0.56 0.68 0.67 0.79	 0.60 0.74 0.69 0.84	V
Maximum Instantaneous Reverse Current (Note 2) (Rated dc Voltage, T_J = 125°C) (Rated dc Voltage, T_J = 25°C)	i_R	 − −	 0.95 0.0013	 5.0 0.1	mA

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

2. Pulse Test: Pulse Width = 300 μs, Duty Cycle ≤ 2%.

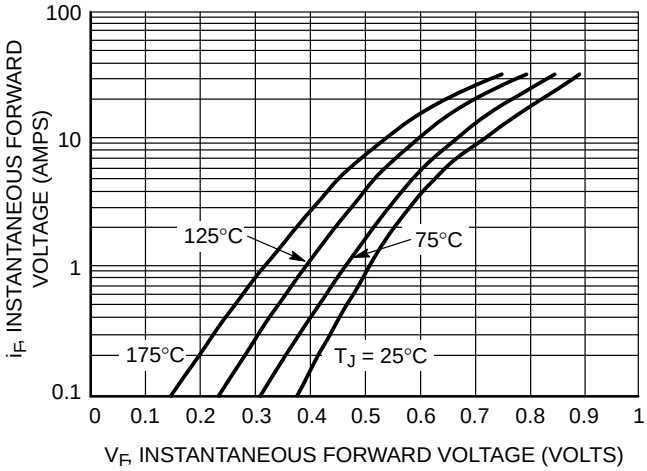


Figure 1. Typical Forward Voltage Per Diode

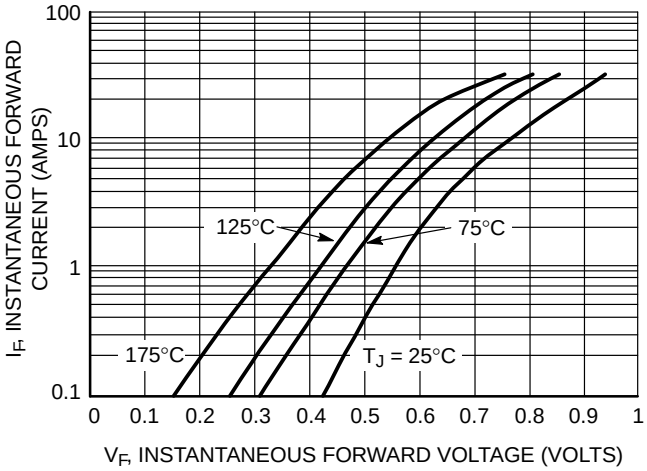


Figure 2. Maximum Forward Voltage Per Diode

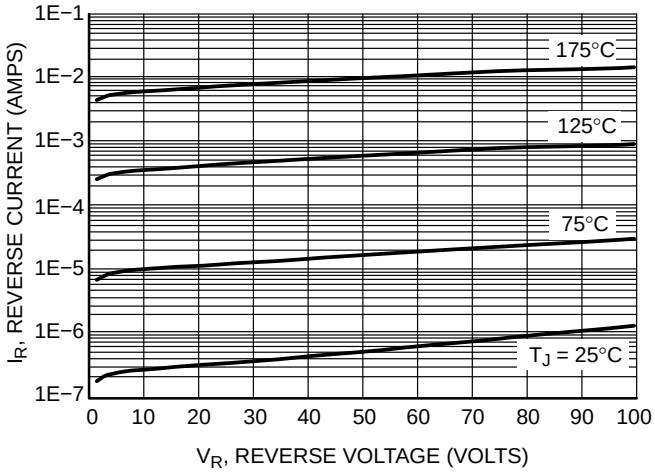


Figure 3. Typical Reverse Current Per Diode

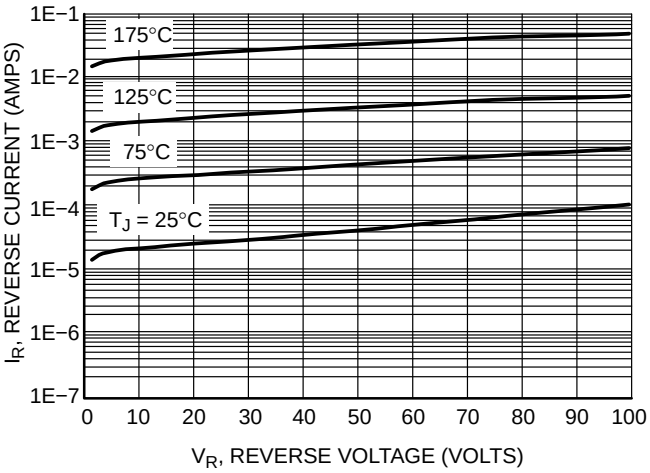


Figure 4. Typical Capacitance Per Diode

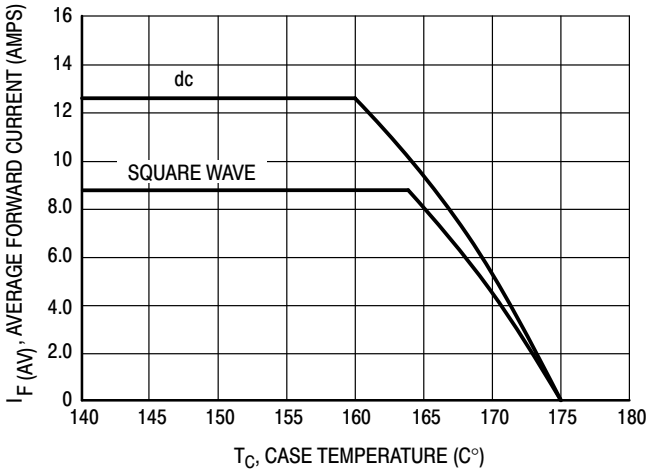


Figure 5. Current Derating, Case Per Leg

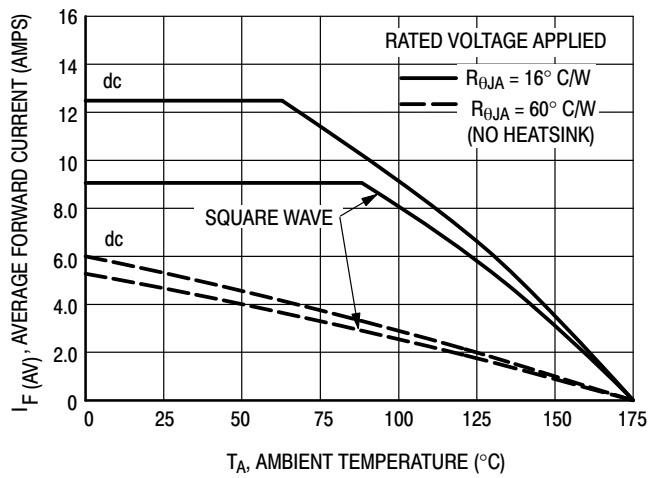


Figure 6. Current Derating, Ambient Per Leg

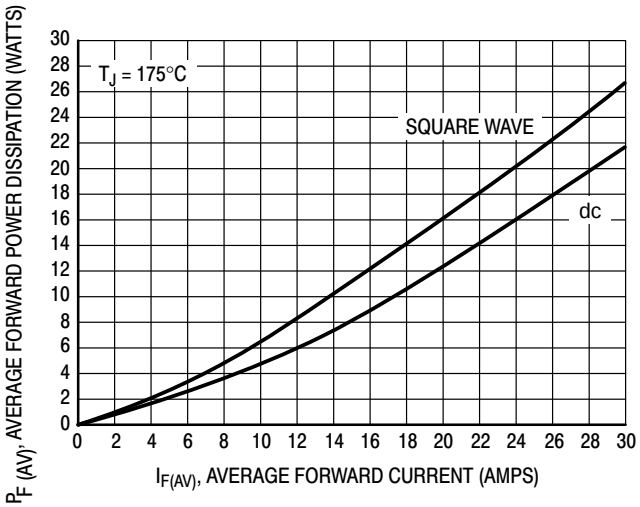


Figure 7. Forward Power Dissipation

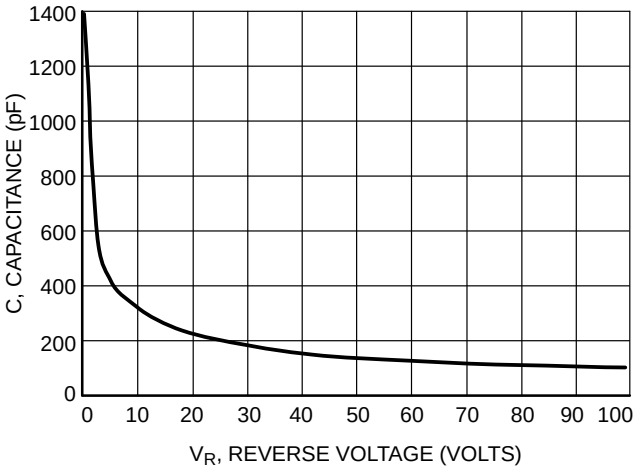
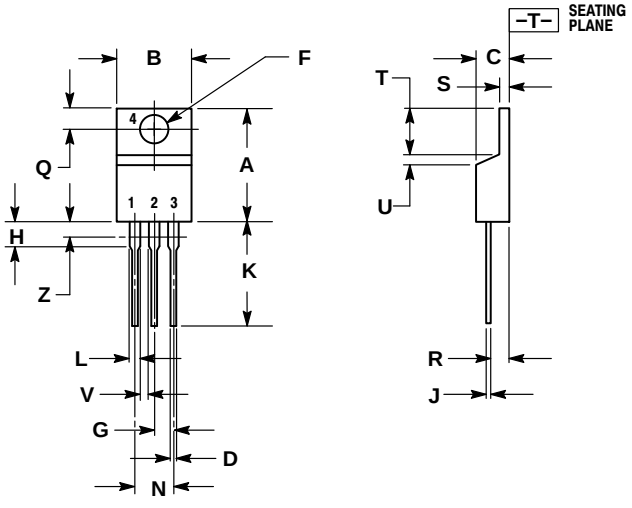


Figure 8. Typical Capacitance Per Diode

MBR16100CTG

PACKAGE DIMENSIONS

TO−220
CASE 221A−09
ISSUE AH



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.570	0.620	14.48	15.75
B	0.380	0.415	9.66	10.53
C	0.160	0.190	4.07	4.83
D	0.025	0.038	0.64	0.96
F	0.142	0.161	3.61	4.09
G	0.095	0.105	2.42	2.66
H	0.110	0.161	2.80	4.10
J	0.014	0.024	0.36	0.61
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.39
T	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
V	0.045	---	1.15	---
Z	---	0.080	---	2.04

STYLE 6:
PIN 1. ANODE
2. CATHODE
3. ANODE
4. CATHODE

ON Semiconductor and the ON are registered trademarks of Semiconductor Components Industries, LLC (SCILLC) or its subsidiaries in the United States and/or other countries. SCILLC owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of SCILLC's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent−Marking.pdf. SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
Literature Distribution Center for ON Semiconductor
P.O. Box 5163, Denver, Colorado 80217 USA
Phone: 303−675−2175 or 800−344−3860 Toll Free USA/Canada
Fax: 303−675−2176 or 800−344−3867 Toll Free USA/Canada
Email: orderlit@onsemi.com

N. American Technical Support: 800−282−9855 Toll Free USA/Canada
Europe, Middle East and Africa Technical Support:
Phone: 421 33 790 2910
Japan Customer Focus Center
Phone: 81−3−5817−1050

ON Semiconductor Website: **www.onsemi.com**

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative

MBR16100CT/D